

BAP1321-02

Silicon PIN diode

Rev. 02 — 3 January 2008

Product data sheet

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NXP Semiconductors

Silicon PIN diode

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FEATURES

- High voltage, current controlled
- RF resistor for RF attenuators and switches
- Low diode capacitance
- Low diode forward resistance
- Very low series inductance
- For applications up to 3 GHz.

APPLICATIONS

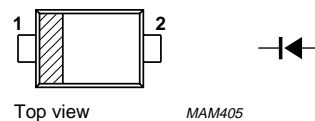
- RF attenuators and switches.

DESCRIPTION

Planar PIN diode in a SOD523 ultra small SMD plastic package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode



Marking code: K7.

Fig.1 Simplified outline (SOD523) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		–	60	V
I_F	continuous forward current		–	100	mA
P_{tot}	total power dissipation	$T_s \leq 90\text{ °C}$	–	715	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–65	+150	°C

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ELECTRICAL CHARACTERISTICST_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _F	forward voltage	I _F = 50 mA	0.95	1.1	V
I _R	reverse leakage current	V _R = 60 V	–	100	nA
C _d	diode capacitance	V _R = 0; f = 1 MHz	0.4	–	pF
		V _R = 1 V; f = 1 MHz	0.35	0.45	pF
		V _R = 20 V; f = 1 MHz	0.25	0.32	pF
r _D	diode forward resistance	f = 100 MHz; note 1			
		I _F = 0.5 mA	3.4	5.0	Ω
		I _F = 1 mA	2.4	3.6	Ω
		I _F = 10 mA	1.2	1.8	Ω
		I _F = 100 mA	0.85	1.3	Ω
S ₂₁ ²	isolation	V _R = 0; f = 900 MHz	16.3	–	dB
		V _R = 0; f = 1800 MHz	11.4	–	dB
		V _R = 0; f = 2450 MHz	9.2	–	dB
S ₂₁ ²	insertion loss	I _F = 0.5 mA; f = 900 MHz	0.23	–	dB
		I _F = 0.5 mA; f = 1800 MHz	0.27	–	dB
		I _F = 0.5 mA; f = 2450 MHz	0.33	–	dB
S ₂₁ ²	insertion loss	I _F = 1 mA; f = 900 MHz	0.18	–	dB
		I _F = 1 mA; f = 1800 MHz	0.22	–	dB
		I _F = 1 mA; f = 2450 MHz	0.27	–	dB
S ₂₁ ²	insertion loss	I _F = 10 mA; f = 900 MHz	0.10	–	dB
		I _F = 10 mA; f = 1800 MHz	0.16	–	dB
		I _F = 10 mA; f = 2450 MHz	0.20	–	dB
S ₂₁ ²	insertion loss	I _F = 100 mA; f = 900 MHz	0.08	–	dB
		I _F = 100 mA; f = 1800 MHz	0.13	–	dB
		I _F = 100 mA; f = 2450 MHz	0.18	–	dB
τ _L	charge carrier life time	when switched from I _F = 10 mA to I _R = 6 mA; R _L = 100 Ω; measured at I _R = 3 mA	0.5	–	μs
L _S	series inductance	I _F = 100 mA; f = 100 MHz	0.6	–	nH

Note

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

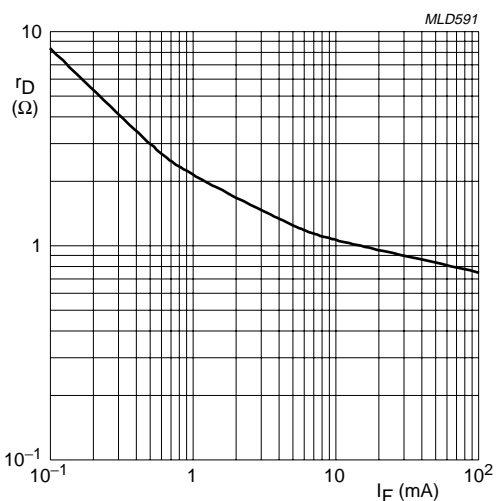
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to soldering point	85	K/W

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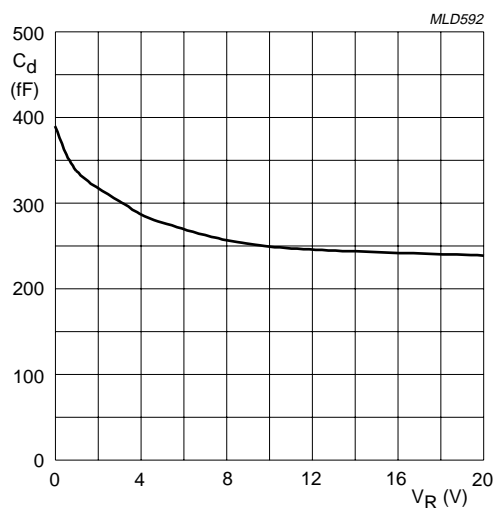
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GRAPHICAL DATA



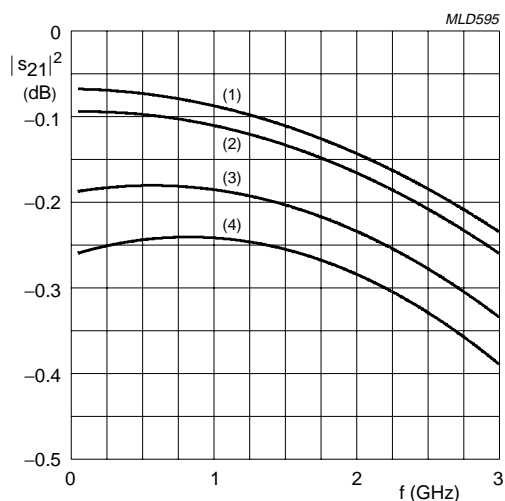
$f = 100$ MHz; $T_j = 25$ °C.

Fig.2 Forward resistance as a function of forward current; typical values.



$f = 1$ MHz; $T_j = 25$ °C.

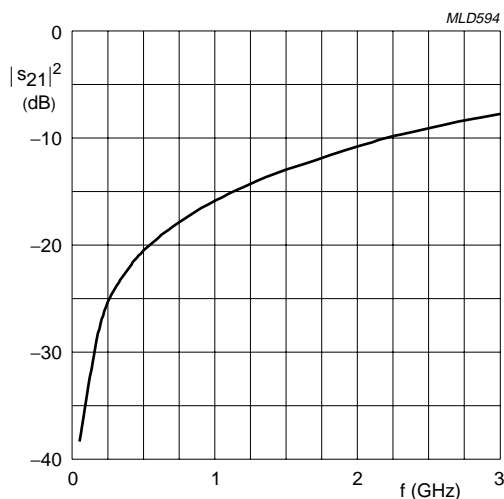
Fig.3 Diode capacitance as a function of reverse voltage; typical values.



- (1) $I_F = 100$ mA. (3) $I_F = 1$ mA.
 (2) $I_F = 10$ mA. (4) $I_F = 0.5$ mA.

Diode inserted in series with a 50 Ω stripline circuit and biased via the analyzer Tee network.
 $T_{amb} = 25$ °C.

Fig.4 Insertion loss ($|s_{21}|^2$) of the diode as a function of frequency; typical values.



Diode zero biased and inserted in series with a 50 Ω stripline circuit.
 $T_{amb} = 25$ °C.

Fig.5 Isolation ($|s_{21}|^2$) of the diode as a function of frequency; typical values.

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PACKAGE OUTLINE

Plastic surface-mounted package; 2 leads

SOD523

0 0.5 1 mm
scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	D	E	H _E	v
mm	0.65 0.58	0.34 0.26	0.17 0.11	1.25 1.15	0.85 0.75	1.65 1.55	0.1

Note
1. The marking bar indicates the cathode.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOD523			SC-79			-02-12-13- 06-03-16

Legal information

Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Revision history

Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BAP1321-02_N_2	20080103	Product data sheet	-	BAP1321-02_1
Modifications:				
• Package outline drawing on page 5 changed				
BAP1321-02_1 (9397 750 08131)	20010417	Product specification	-	-

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